

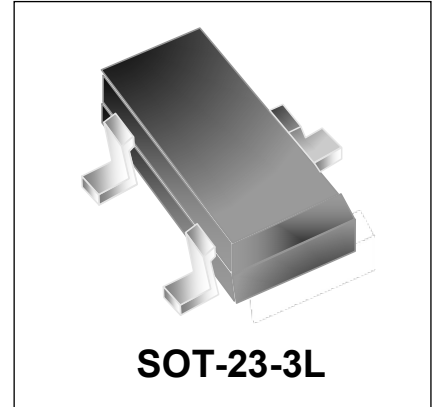
## N-Channel MOSFET

### Features

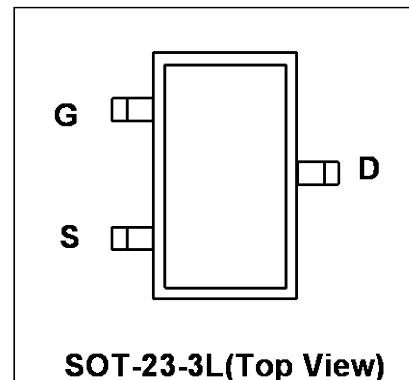
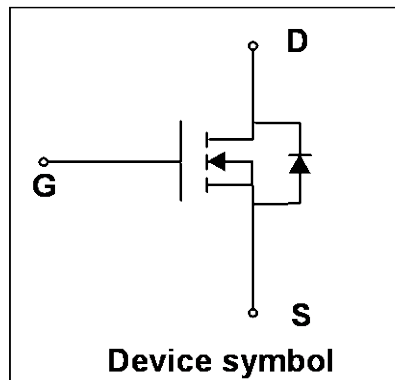
- $V_{DS} = 30V$ ,  $I_D = 5.8A$   
 $R_{DS(on)} < 35m\Omega$  @  $V_{GS} = 10V$   
 $R_{DS(on)} < 40m\Omega$  @  $V_{GS} = 4.5V$
- High Dense Cell Design for Extremely Low  $R_{DS(ON)}$
- Exceptional On-resistance and Maximum DC Current Capability

### Mechanical Characteristics

- SOT-23-3L Package
- Marking : Making Code
- RoHS Compliant



### Schematic & PIN Configuration



### Absolute Maximum Rating( $T_{amb}=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	5.8	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	30	A
Power Dissipation <sup>1</sup>	$P_D$	1.5	W
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$
Thermal Resistance from Junction to Ambient <sup>2</sup>	$R_{\theta JA}$	83.3	$^{\circ}C/W$

Electrical Characteristics (T<sub>amb</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	<b>BV<sub>DSS</sub></b>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250μA	30	-	-	V
Drain Cut-off Current	<b>I<sub>DSS</sub></b>	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0 V	-	-	1	μA
Gate leakage Current	<b>I<sub>GSS</sub></b>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12V	-	-	±100	nA
Gate Threshold Voltage <sup>3</sup>	<b>V<sub>GS(th)</sub></b>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.7	0.9	1.4	V
Drain-Source on-state Resistance <sup>3</sup>	<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.8A	-	29	35	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A	-	32	40	
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4A	-	40	52	
<b>Dynamic Characteristics</b>						
Input Capacitance	<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz	-	670	-	pF
Output Capacitance	<b>C<sub>oss</sub></b>		-	99	-	
Reverse Transfer Capacitance	<b>C<sub>rss</sub></b>		-	77	-	
<b>Switching Characteristics</b>						
Turn-on Time <sup>4</sup>	<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>L</sub> = 2.7Ω, R <sub>GEN</sub> = 3Ω	-	5	-	nS
Rise time <sup>4</sup>	<b>t<sub>r</sub></b>		-	7	-	
Turn-off Time <sup>4</sup>	<b>t<sub>d(off)</sub></b>		-	40	-	
Fall time <sup>4</sup>	<b>t<sub>f</sub></b>		-	6	-	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Diode Forward Voltage <sup>3</sup>	<b>V<sub>SD</sub></b>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	-	-	1	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 board using 1 square inch pad size, 1oz single-side copper.
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
4. Guaranteed by design, not subject to product.

Typical Characteristics

Figure 1. Output Characteristics

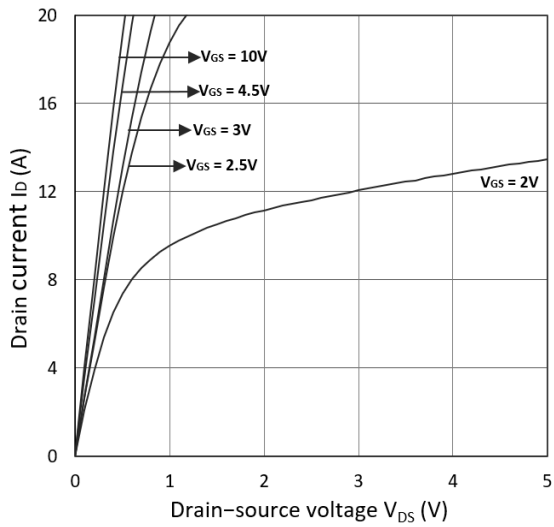


Figure 2. Transfer Characteristics

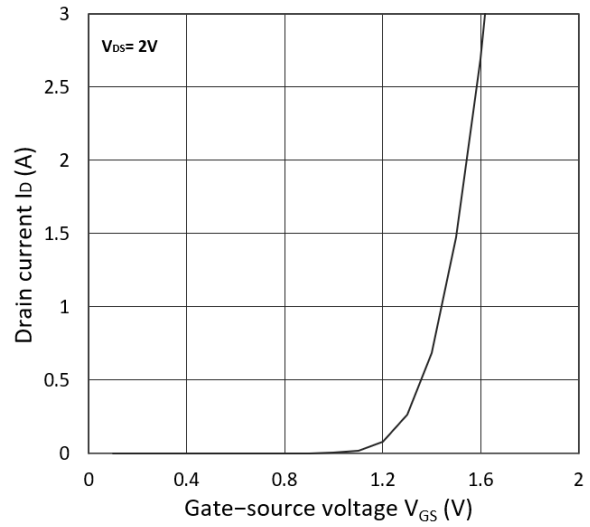


Figure 3.  $R_{DS(on)}$  vs.  $I_D$

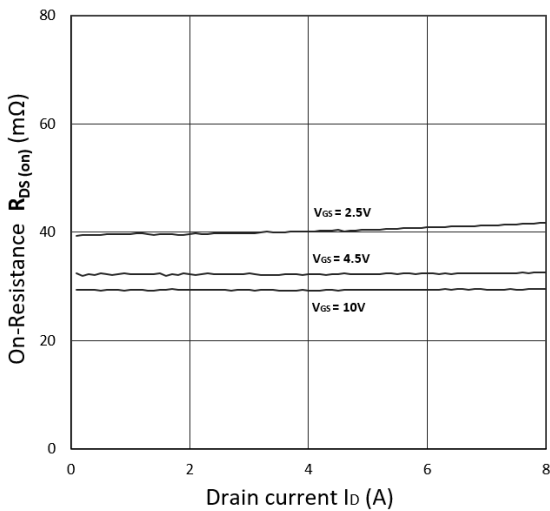


Figure 4.  $R_{DS(on)}$  vs.  $V_{GS}$

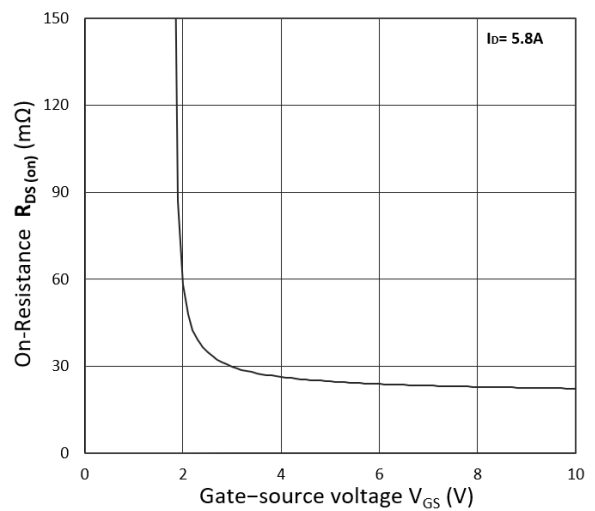


Figure 5.  $I_S$  vs.  $V_{SD}$

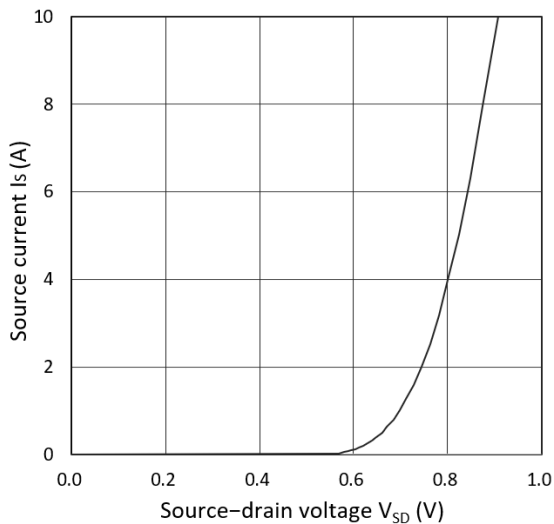
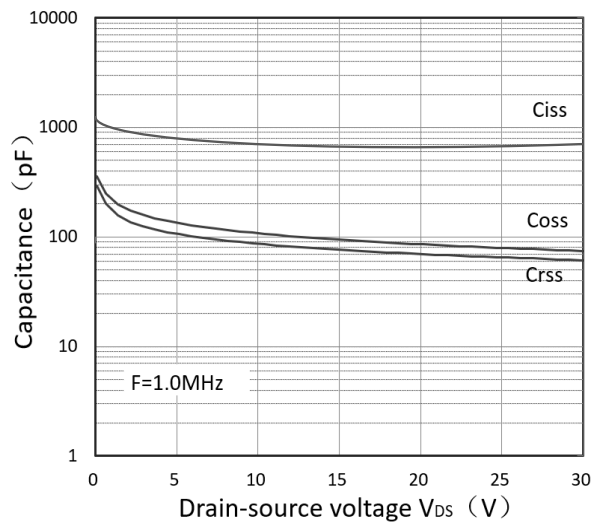


Figure 6. Capacitance Characteristics



Outline Drawing – SOT-23-3L

**PACKAGE OUTLINE**

**SOT-23-3L**

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	1.05	1.15	0.041	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.82	3.02	0.111	0.119
E	2.65	2.95	0.104	0.116
E1	1.50	1.70	0.059	0.067
e	0.95 BSC		0.0374 BSC	
e1	1.80	2.00	0.071	0.079
L	0.55	0.75	0.021	0.029
θ	0	8°	0	8°

Unit:mm

**Notes**

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Dimensions are exclusive of mold flash and metal burrs.

**Marking Codes**

Part Number	WM03N58M2
Marking Code	

**Package Information**

Qty: 3k/Reel

**CONTACT INFORMATION**

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.  
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.  
Users should verify actual device performance in their specific applications.